Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS303PX.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	10.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	31	44	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1 SOT89	B — E sym042

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PBSS303NX	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS303NX	%5D

[1] % = placeholder for manufacturing site code

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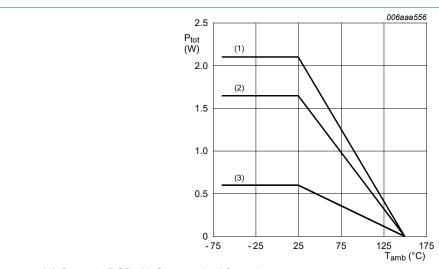
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	30	V
V _{CEO}	collector-emitter voltage	open base		-	30	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	10.2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint. [3]



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves**

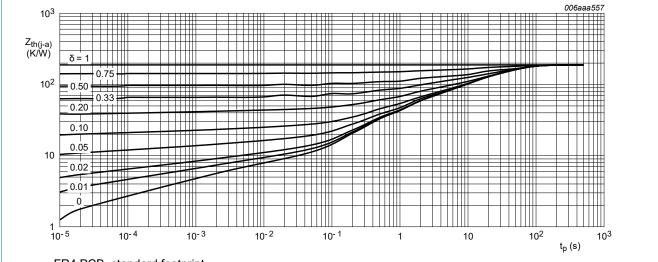
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistant junction to ambie	thermal resistance from	in free air	[1]	-	-	208	K/W
	junction to ambient		[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

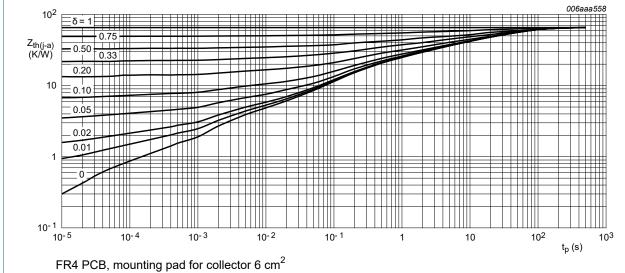
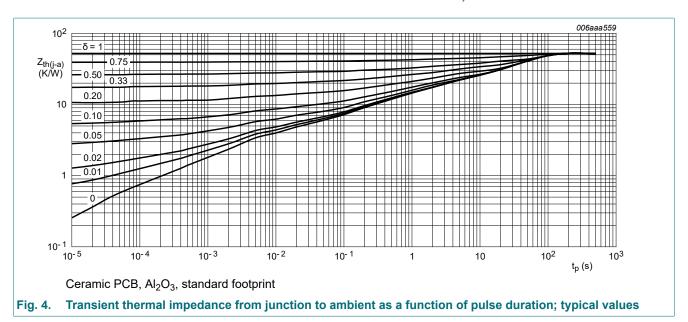


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	$ \begin{array}{c} \text{tter-base cut-off} \\ \text{tert-base cut-off} \\ \text{tert} \\ \text{current gain} \\ \\ \\ V_{CB} = 2 \ V; \ I_{C} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 0.5 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 1 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 2 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 4 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 4 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 4 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 6 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 6 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ V_{CE} = 2 \ V; \ I_{C} = 6 \ A; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 1 \ A; \ I_{B} = 50 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 1 \ A; \ I_{B} = 50 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 1 \ A; \ I_{B} = 10 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 4 \ A; \ I_{B} = 400 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 4 \ A; \ I_{B} = 400 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 4 \ A; \ I_{B} = 400 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 4 \ A; \ I_{B} = 200 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = 4 \ A; \ I_{B} = 200 \ \text{mA}; \ \text{pulsed}; \ t_{p} \leq 300 \ \mu \text{s}; \ \delta \leq 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ \\ I_{C} = $	-			
			300	460	-	
			250	430	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	360	-	
			180	270	-	
V _{CEsat}	collector-emitter saturation voltage		-	20	30	mV
			-	40	60	mV
			-	60	90	mV
			-	80	110	mV
			-	125	175	mV
			-	120	170	mV
			-	160	250	mV
			-	150	220	mV
R _{CEsat}	collector-emitter saturation resistance		-	31	44	mΩ
			-	40	63	mΩ
V _{BEsat}	base-emitter saturation voltage		-	0.81	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.95	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 0.15 A;	-	15	-	ns
t _r	rise time	I _{Boff} = -0.15 A; T _{amb} = 25 °C	-	50	-	ns
t _{on}	turn-on time		-	65	-	ns
-s	storage time	1	-	305	-	ns
t _f	fall time		-	70	-	ns
t _{off}	turn-off time	1	-	375	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 0.1 A; f = 100 MHz; T_{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	60	100	pF

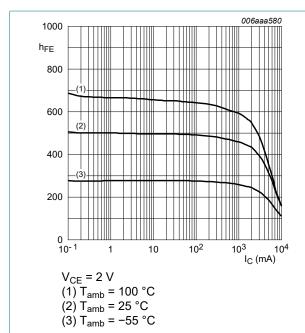


Fig. 5. DC current gain as a function of collector current; typical values

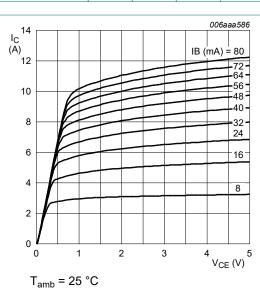


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

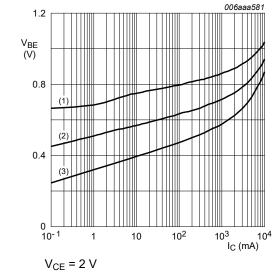
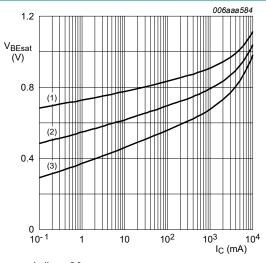




Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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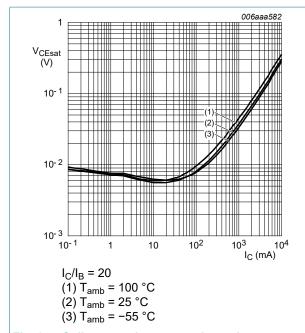


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

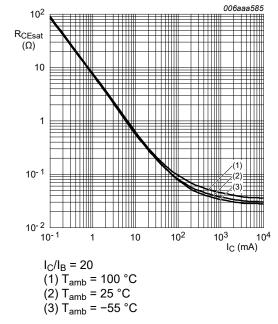


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

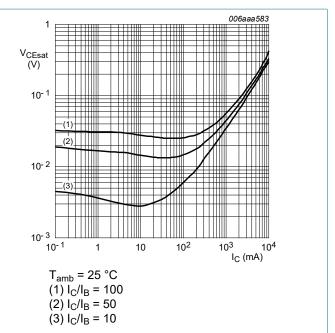


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

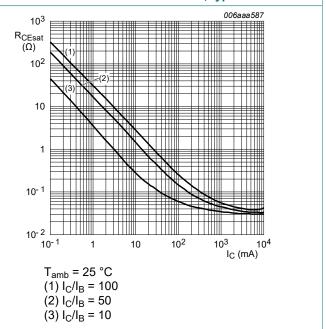
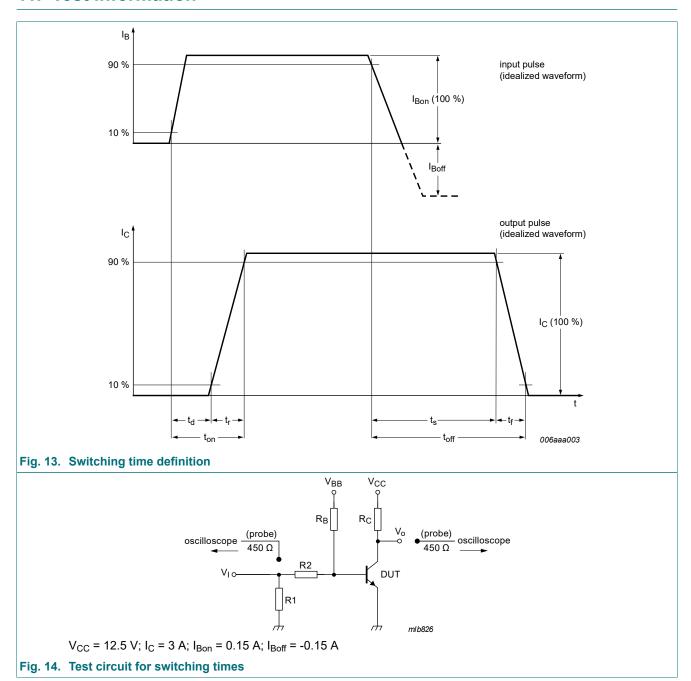


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

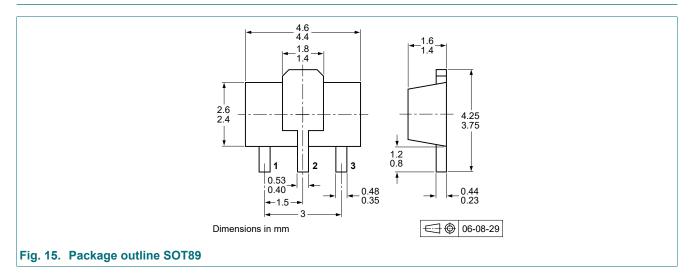


Quality information

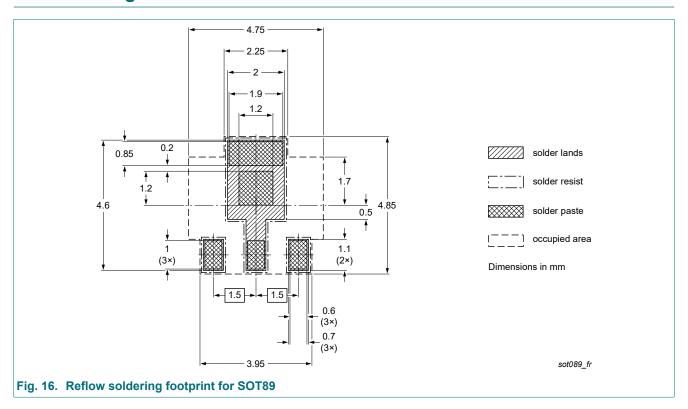
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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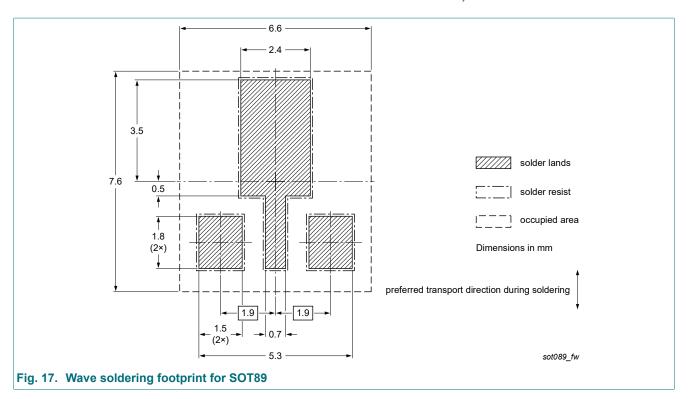
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS303NX v.3	20240219	Product data sheet	-	PBSS303NX_2	
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 				
PBSS303NX_2	20091120	Product data sheet	-	PBSS303NX_1	
PBSS303NX_1	20060823	Product data sheet	-	-	

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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